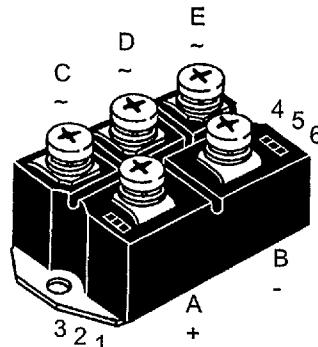
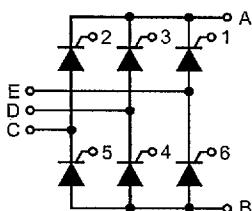


Three Phase Full Controlled Rectifier Bridge, B6C

$$I_{dAVM} = 110/167 \text{ A}$$

$$V_{RRM} = 1200-1600 \text{ V}$$

V_{RSM}	V_{RRM}	Type
V_{DSM}	V_{DRM}	
V	V	
1300	1200	VTO 110-12io7
1500	1400	VTO 110-14io7
1700	1600	VTO 175-16io7



Symbol	Test Conditions	Maximum Ratings	
		VTO 110	VTO 175
I_{dAV}	$T_c = 85^\circ\text{C}$; module per leg	110	167
I_{FRMS}, I_{TRMS}		58	89
I_{FSM}, I_{TSM}	$T_{vj} = 45^\circ\text{C}$; $t = 10 \text{ ms}$ (50 Hz), sine $V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	1150	1500
	$T_{vj} = T_{vjm}$ $V_R = 0$ $t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	1230	1600
I^2t	$T_{vj} = 45^\circ\text{C}$ $V_R = 0$ $t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	6600	11200
	$T_{vj} = T_{vjm}$ $V_R = 0$ $t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	6280	10750
$(di/dt)_cr$	$T_{vj} = T_{vjm}$ $f = 400 \text{ Hz}$, $t_p = 200 \mu\text{s}$ $V_D = 2/3 V_{DRM}$ $I_G = 0.3 \text{ A}$, non repetitive $di_G/dt = 0.3 \text{ A}/\mu\text{s}$, $I_T = 1/3 \cdot I_{dAV}$	150	A/ μs
$(dv/dt)_cr$	$T_{vj} = T_{vjm}$; $V_{DR} = 2/3 V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	1000	V/ μs
V_{RGM}		10	V
P_{GM}	$T_{vj} = T_{vjm}$ $I_T = I_{TAVM}$ $t_p = 30 \mu\text{s}$ $t_p = 500 \mu\text{s}$ $t_p = 10 \text{ ms}$	≤ 10 ≤ 5 ≤ 1 0.5	W
P_{GAVM}		-40...+125 125 -40...+125	°C
T_{vj}		-40...+125	°C
T_{vjm}		125	°C
T_{stg}		-40...+125	°C
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	2500 3000	V-
M_d	Mounting torque (M6) Terminal connection torque (M6)	5-15 5-15	Nm lb.in.
Weight	typ.	300	g

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.
IXYS reserves the right to change limits, test conditions and dimensions.

Symbol	Test Conditions	Characteristic Values		
		VTO 110	VTO 175	
I_R, I_D	$V_R = V_{RRM}$; $V_D = V_{DRM}$	$T_{VJ} = T_{VJM}$	≤ 5	mA
		$T_{VJ} = 25^\circ\text{C}$	≤ 0.3	mA
V_F, V_T	$I_F = I_T = 200 \text{ A}$, $T_{VJ} = 25^\circ\text{C}$		≤ 1.75	1.57
V_T	For power-loss calculations only		0.85	V
r_T	($T_{VJ} = 125^\circ\text{C}$)		6	$\text{m}\Omega$
V_{GT}	$V_D = 6 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$		≤ 1.5	V
	$T_{VJ} = -40^\circ\text{C}$		≤ 1.6	V
I_{GT}	$V_D = 6 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$		≤ 100	mA
	$T_{VJ} = -40^\circ\text{C}$		≤ 200	mA
V_{GD}	$T_{VJ} = T_{VJM}$	$V_D = 2/3 V_{DRM}$	≤ 0.2	V
I_{GD}	$T_{VJ} = T_{VJM}$	$V_D = 2/3 V_{DRM}$	≤ 5	mA
I_L	$I_G = 0.3 \text{ A}$; $t_G = 30 \mu\text{s}$	$T_{VJ} = 25^\circ\text{C}$	≤ 450	mA
		$dI_G/dt = 0.3 \text{ A}/\mu\text{s}$		
I_H	$T_{VJ} = 25^\circ\text{C}$; $V_D = 6 \text{ V}$; $R_{GK} = \infty$		≤ 200	mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}$; $V_D = 1/2 V_{DRM}$		≤ 2	μs
	$I_G = 0.3 \text{ A}$; $dI_G/dt = 0.3 \text{ A}/\mu\text{s}$			
R_{thJC}	per thyristor (diode); DC current	0.65	0.46	K/W
	per module	0.108	0.077	K/W
R_{thJH}	per thyristor (diode); DC current	0.8	0.55	K/W
	per module	0.133	0.092	K/W
d_s	Creeping distance on surface	10	mm	
d_A	Creepage distance in air	9.4	mm	
a	Max. allowable acceleration	50	m/s^2	

Dimensions in mm (1 mm = 0.0394")

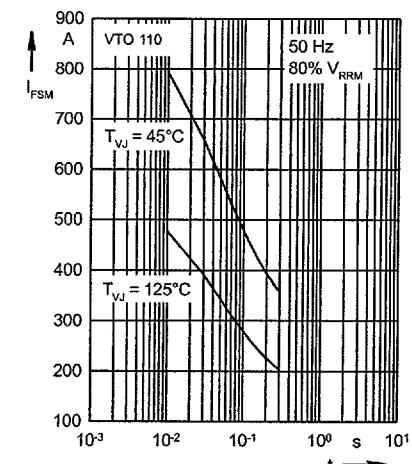
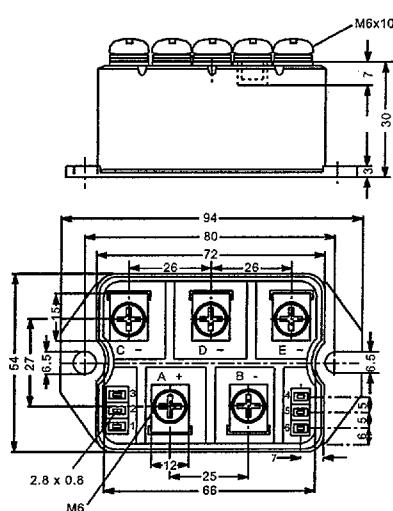


Fig. 3 Surge overload current
 I_{FSM} : Crest value, t : duration

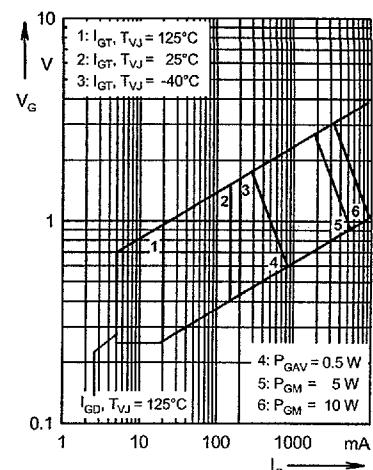


Fig. 1 Gate trigger characteristics

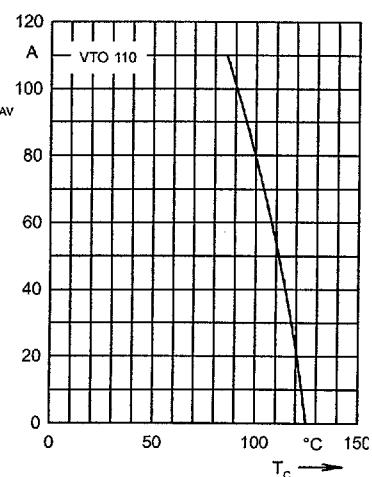


Fig. 2 DC output current at case temperature

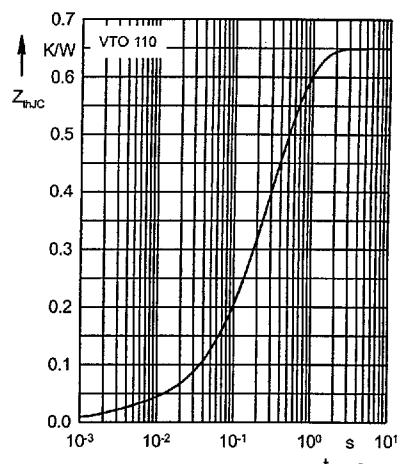


Fig. 4 Transient thermal impedance junction to case (per leg)